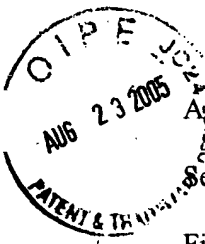


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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Applicant: Chien-Chao Huang, et al.
Serial No.: 10/710,012
Filed: June 11, 2004
For: Improved Cobalt Silicidation
Process for Substrates with a
Germanium Layer

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Docket No.: 2001.1531 / 24061.439
Examiner: Matthew C. Landau
Art Unit: 2815
Conf. No.: 4011

RESPONSE TO RESTRICTION REQUIREMENT

Commissioner for Patents
Mail Stop: Amendment
PO Box 1450
Alexandria, VA 22313-1450

Dear Sir:

The present paper is being submitted in response to the Restriction Requirement Office Action dated July 28, 2005 in the above-identified application.

Election of Claims begins on page 2 of this paper.

Amendments to the Claims are reflected in the Listing of Claims which begins on page 3 of this paper.

Remarks begin on page 9 of this paper.

I. Election

In the Office Action mailed July 28, 2005, the Examiner alleges that the application contains claims directed to two inventions and, thus, required restriction of either:

Group I: Claims 30-33, drawn to a semiconductor device; and

Group II: Claims 1-29, drawn to a method of making a semiconductor device;

In response, Applicants hereby elect Group II, corresponding to claims 1-29. Applicants' election is made with traverse on the grounds that the embodiments delineated by the Examiner are not patentably distinct and therefore constitute a single invention concept.